



### Product Summary

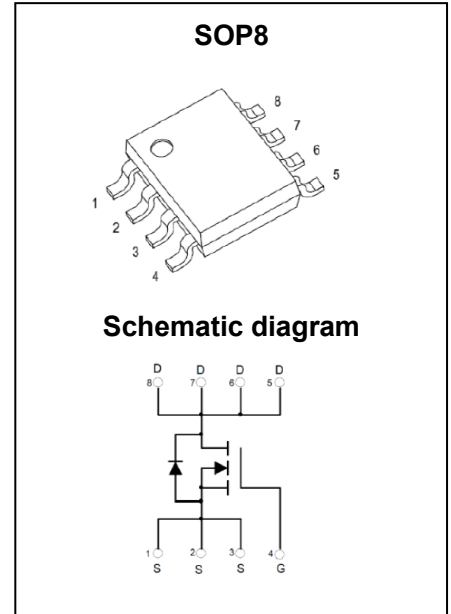
$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
100V	7.7m $\Omega$ @10V	60A
	10.5m $\Omega$ @4.5V	

### Feature

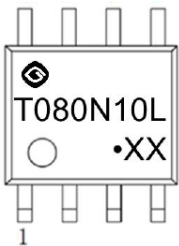
- Split Gate Trench Technology
- Low  $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

### Application

- Power Switching Application



### MARKING:



T080N10L = Device Code  
 XX = Date Code  
 Solid Dot = Green Indicator

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain - Source Voltage	$V_{DS}$	100	V	
Gate - Source Voltage	$V_{GS}$	$\pm 20$	V	
Continuous Drain Current <sup>1</sup>	$T_C = 25^\circ\text{C}$	$I_D$	60	A
	$T_C = 100^\circ\text{C}$	$I_D$	42	A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	180	A	
Single Pulsed Avalanche Current <sup>3</sup>	$I_{AS}$	31	A	
Single Pulsed Avalanche Energy <sup>3</sup>	$E_{AS}$	145	mJ	
Power Dissipation <sup>5</sup>	$T_C = 25^\circ\text{C}$	$P_D$	5.2	W
Thermal Resistance from Junction to Ambient <sup>6</sup>	$T_A = 25^\circ\text{C}$	$R_{\theta JA}$	75	$^\circ\text{C/W}$
Thermal Resistance from Junction to Case		$R_{\theta JC}$	24	$^\circ\text{C/W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$	
Storage Temperature	$T_{STG}$	-55~ +150	$^\circ\text{C}$	

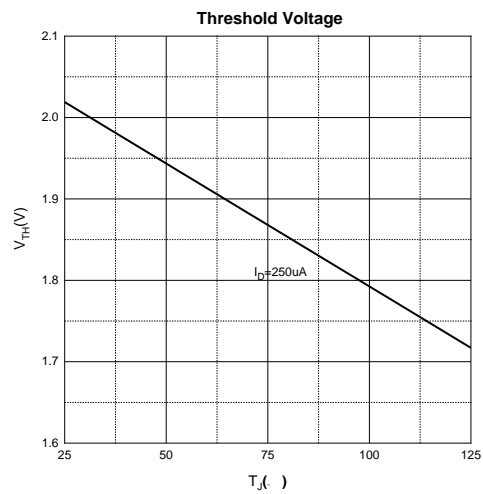
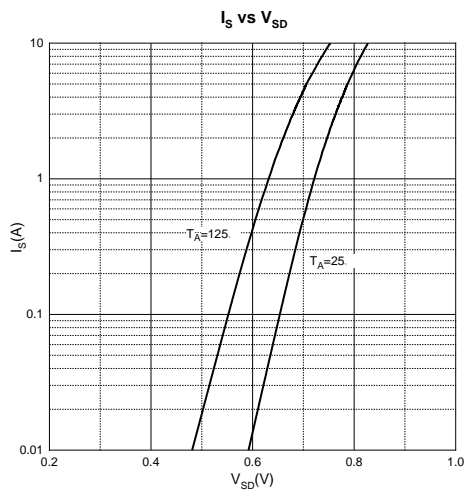
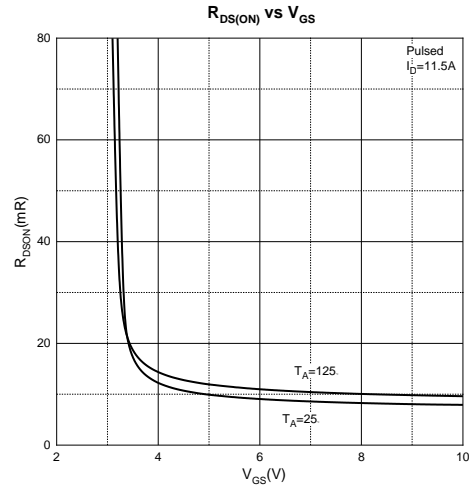
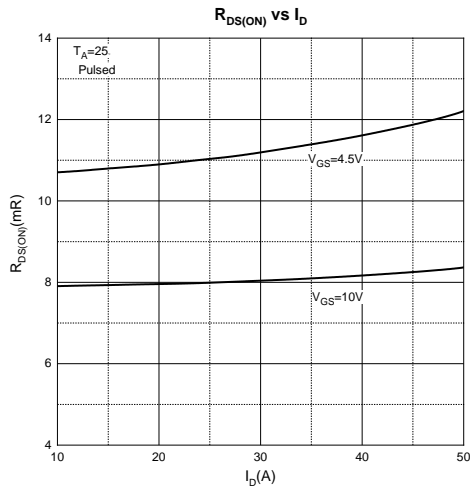
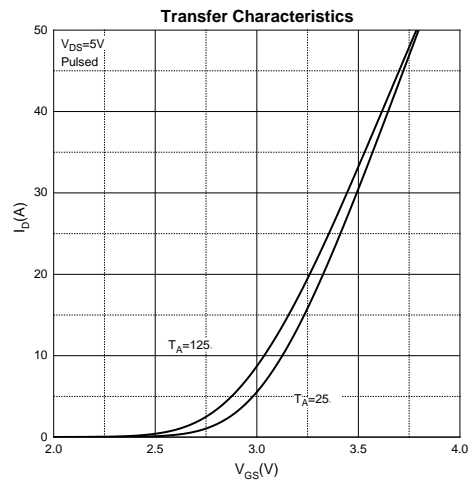
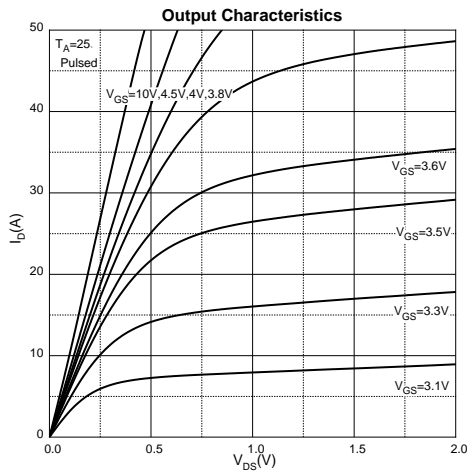
## MOSFET ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Off Characteristics</b>						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 100V, V_{GS} = 0V$			1	$\mu A$
Gate - Body Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$	nA
<b>On Characteristics<sup>4</sup></b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	2	3	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 11.5A$		7.7	12	m $\Omega$
		$V_{GS} = 4.5V, I_D = 9.5A$		10.5	16	
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 50V, V_{GS} = 0V, f = 1MHz$		2188		pF
Output Capacitance	$C_{oss}$			514		
Reverse Transfer Capacitance	$C_{rss}$			23		
Gate Resistance	$R_g$	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		1.5		$\Omega$
<b>Switching Characteristics</b>						
Total Gate Charge	$Q_g$	$V_{DD} = 50V, V_{GS} = 10V, I_D = 11.5A$		38.5		nC
Gate-source Charge	$Q_{gs}$			6.5		
Gate-drain Charge	$Q_{gd}$			9.6		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 50V, V_{GS} = 10V, I_D = 11.5A$ $R_G = 3\Omega$		10		ns
Turn-on Rise Time	$t_r$			5		
Turn-off Delay Time	$t_{d(off)}$			35		
Turn-off Fall Time	$t_f$			5		
<b>Source - Drain Diode Characteristics</b>						
Diode Forward Voltage <sup>4</sup>	$V_{SD}$	$V_{GS} = 0V, I_S = 1A$			1.2	V

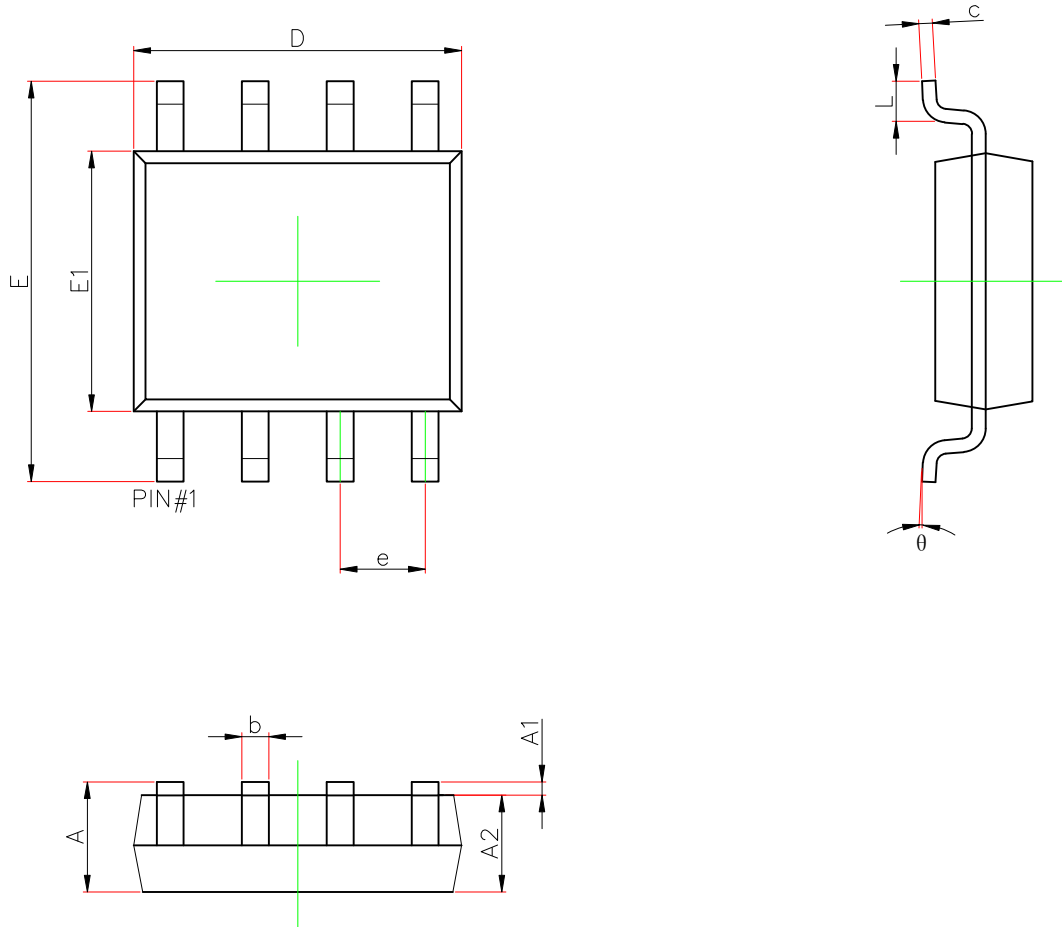
### Notes :

- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width  $\leq 10\mu s$ , duty cycle  $\leq 1\%$ .
- 3.EAS condition:  $V_{DD} = 50V, V_{GS} = 10V, L = 0.3mH, R_G = 25\Omega$  Starting  $T_J = 25^\circ\text{C}$ .
- 4.Pulse Test : Pulse Width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
- 5.The power dissipation  $P_D$  is limited by  $T_{J(MAX)} = 150^\circ\text{C}$ .And device mounted on a large heatsink
- 6.Device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ\text{C}$ .

**Typical Characteristics**



## SOP8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.156	0.250	0.006	0.010
D	4.700	5.100	0.185	0.201
e	1.270(BSC)		0.050(BSC)	
E	5.800	6.200	0.228	0.244
E1	3.700	4.100	0.146	0.161
L	0.400	1.270	0.016	0.05
theta	0°	8°	0°	8°